

Supporting Information

for

Ion Implantation as an Approach for Structural Modifications and Functionalization of $Ti_3C_2T_x$ MXenes

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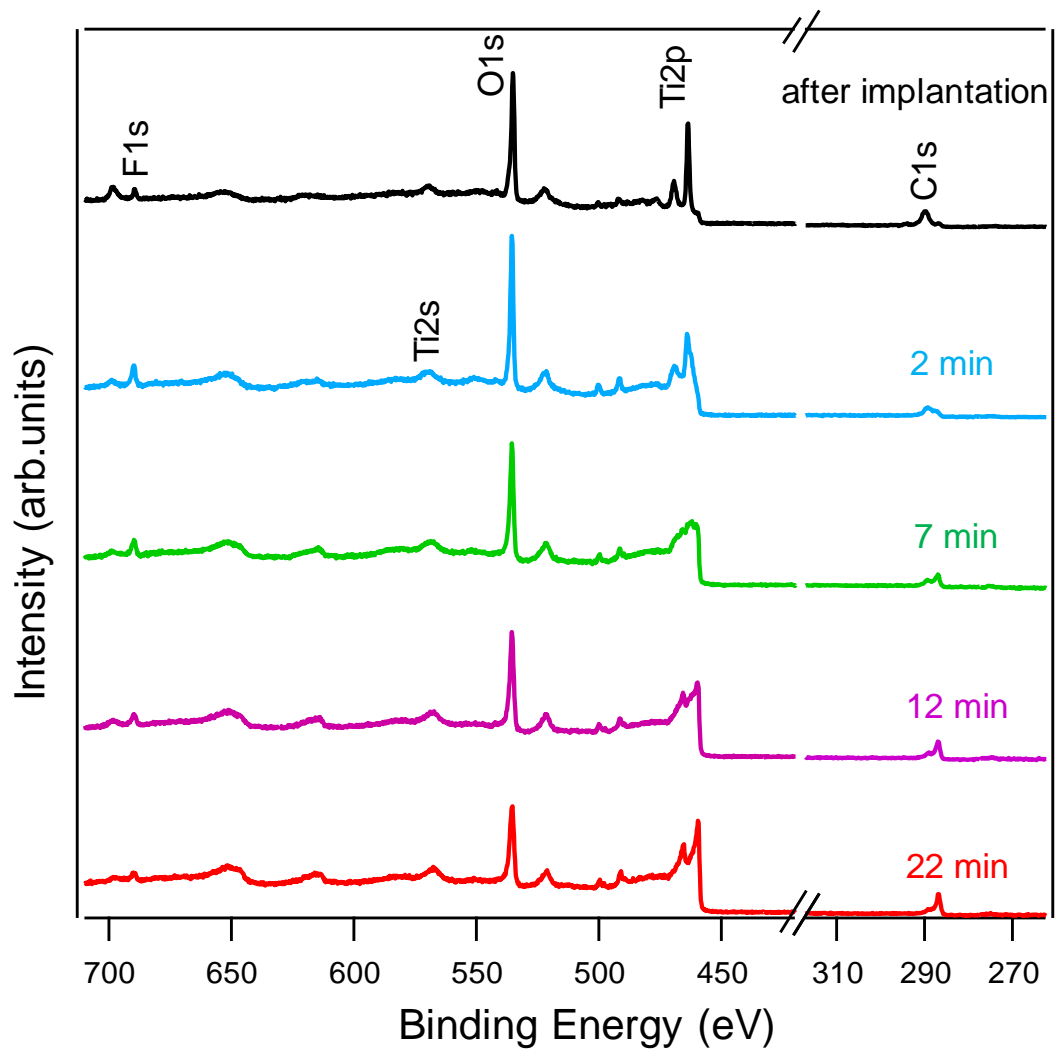


Figure S1. The survey XPS spectra taken on a spin-coated $\text{Ti}_3\text{C}_2\text{T}_x$ film after implantation with $1 \cdot 10^{15}$ Mn-ions/ cm^2 at 60 keV and after different 0.5 keV Ar^+ sputtering cycles carried out to remove each time the exposed film surface and have access to the underneath layer.

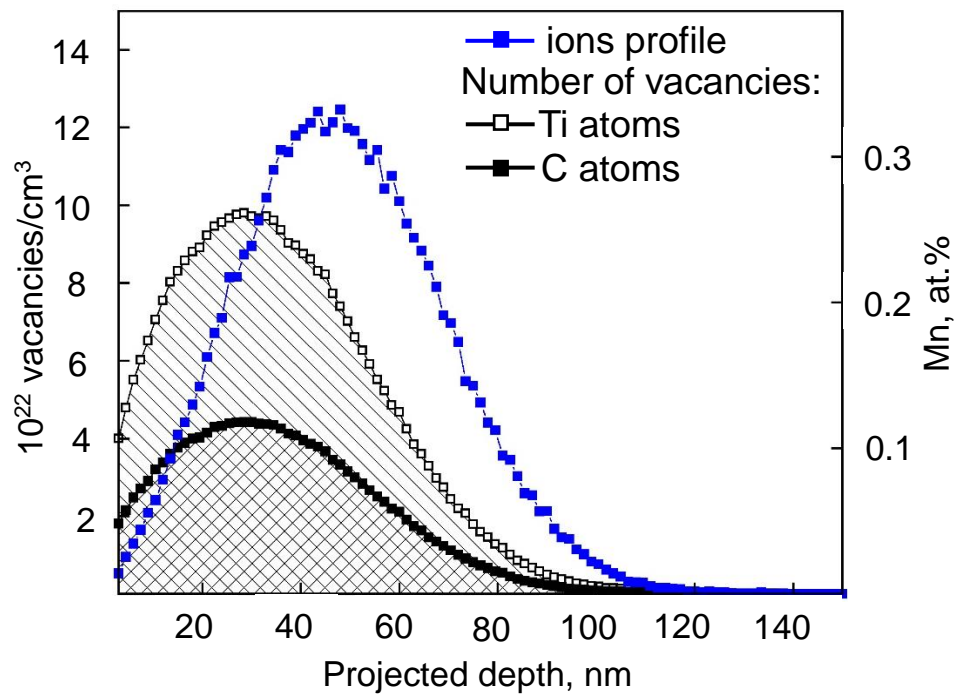


Figure S2. The SRIM simulated depth profiles of Ti and C vacancies (black curves) and Mn⁺-ions distribution (blue curve) within the Ti₃C₂T_x thin film following the ion-implantation with 1·10¹⁵ ions/cm² fluence at 60 keV energy, showing the maximum Mn concentration of ~0.32 at.%.

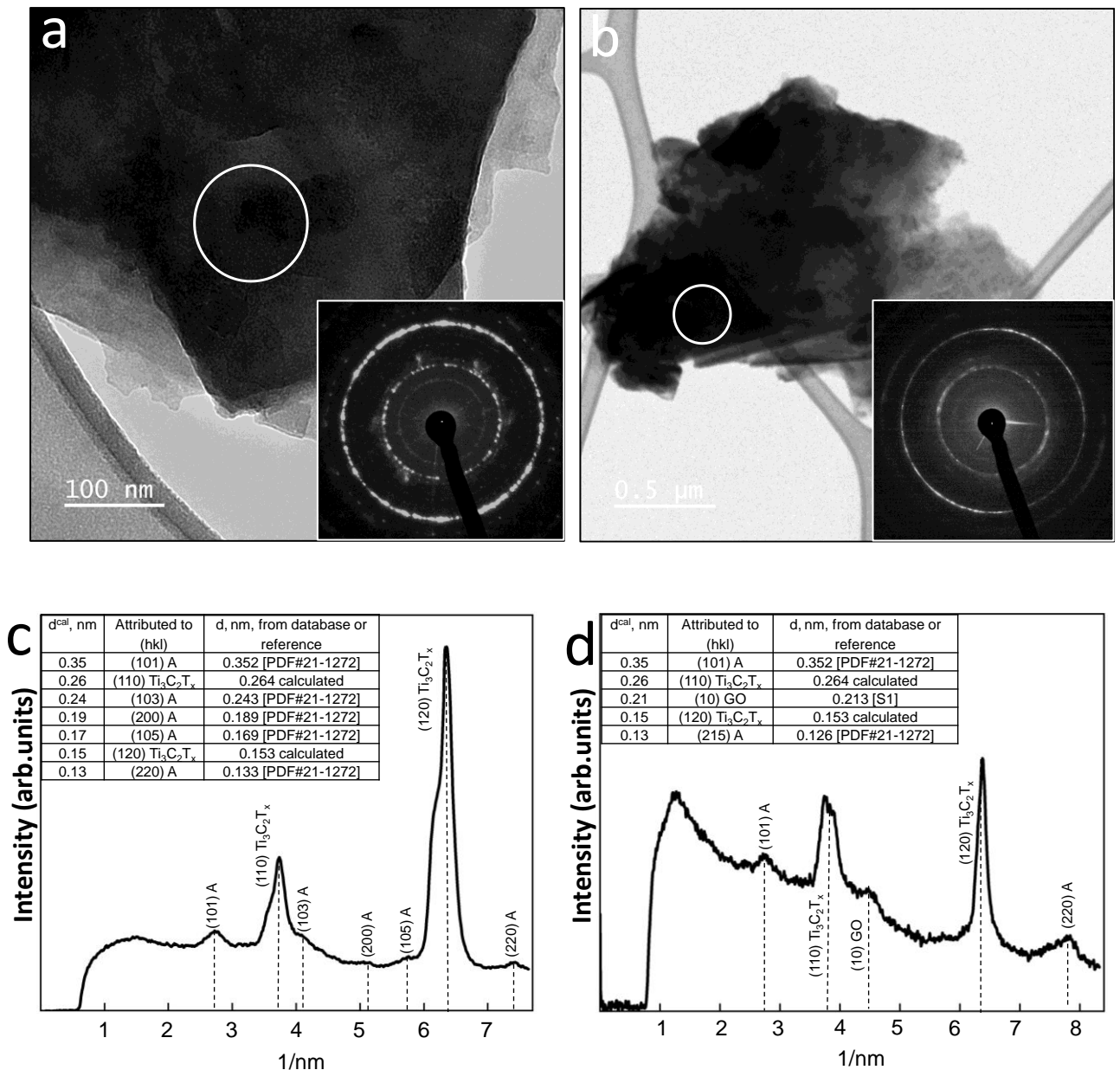


Figure S3. The TEM micrograph of thick parts extracted from the spin-coated $\text{Ti}_3\text{C}_2\text{T}_x$ films implanted at $1 \cdot 10^{15}$ (a) and $1 \cdot 10^{16}$ ions/cm² (b) at 60 keV and corresponding energy-filtered (10 eV slit) SAED patterns (insets). (c), (d) The radial intensity profiles of the SAED patterns presented in insets in (a) and (b). d-spacing values, d^{cal} , are calculated from experimental SAED patterns (a, b, insets). Reference values of d-spacings for anatase (A) were taken from JCPDS database – PDF#21-1272. Reference values of d-spacings for graphene oxide (GO) were taken from the Reference S1.

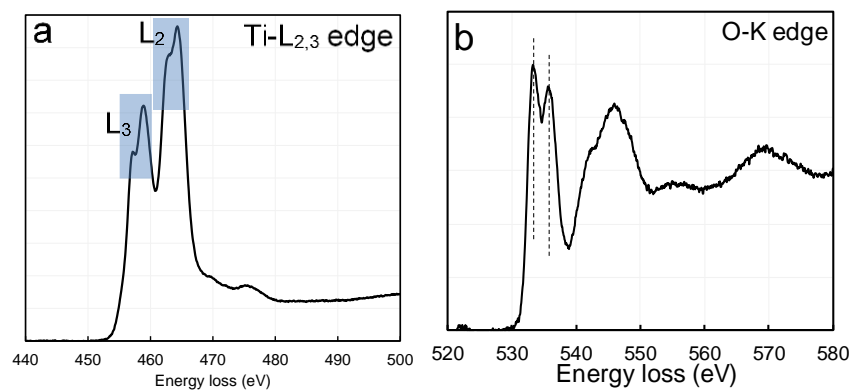


Figure S4. The Ti-L_{2,3} (a), and O-K edge (b) EEL spectra of oxidized Ti₃C₂T_x flakes.

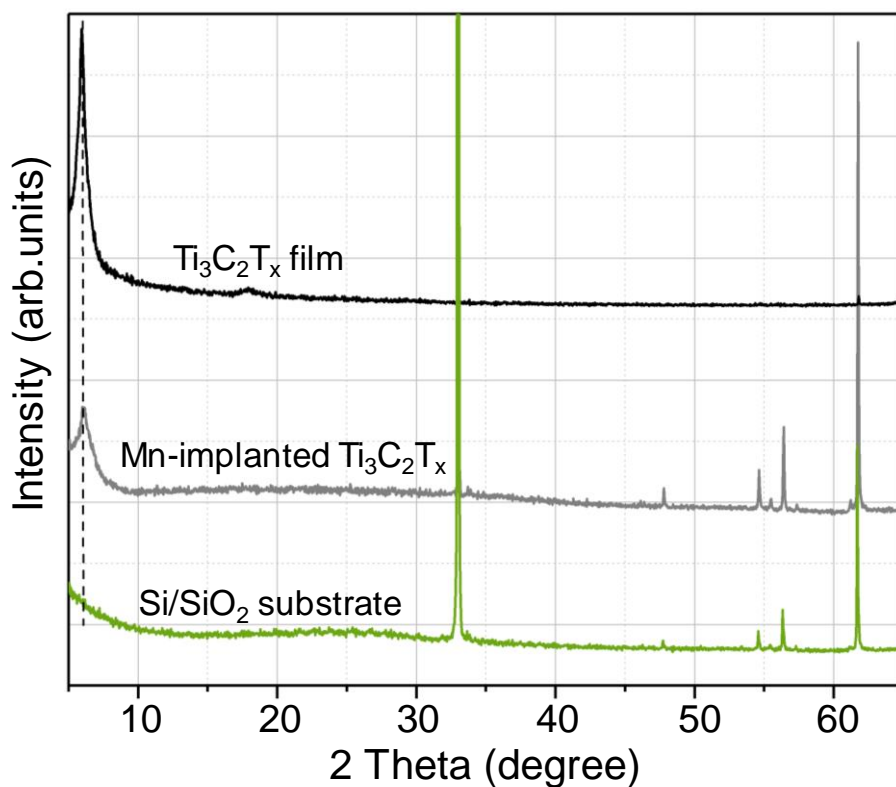


Figure S5. XRD patterns of the Ti₃C₂T_x spin-coated film before implantation (black curve), Ti₃C₂T_x films implanted with $1 \cdot 10^{15}$ Mn-ions/cm² at 60 keV (grey curve). The bottom curve shows, for comparison, the XRD pattern of the Si/SiO₂ substrate (green curve).

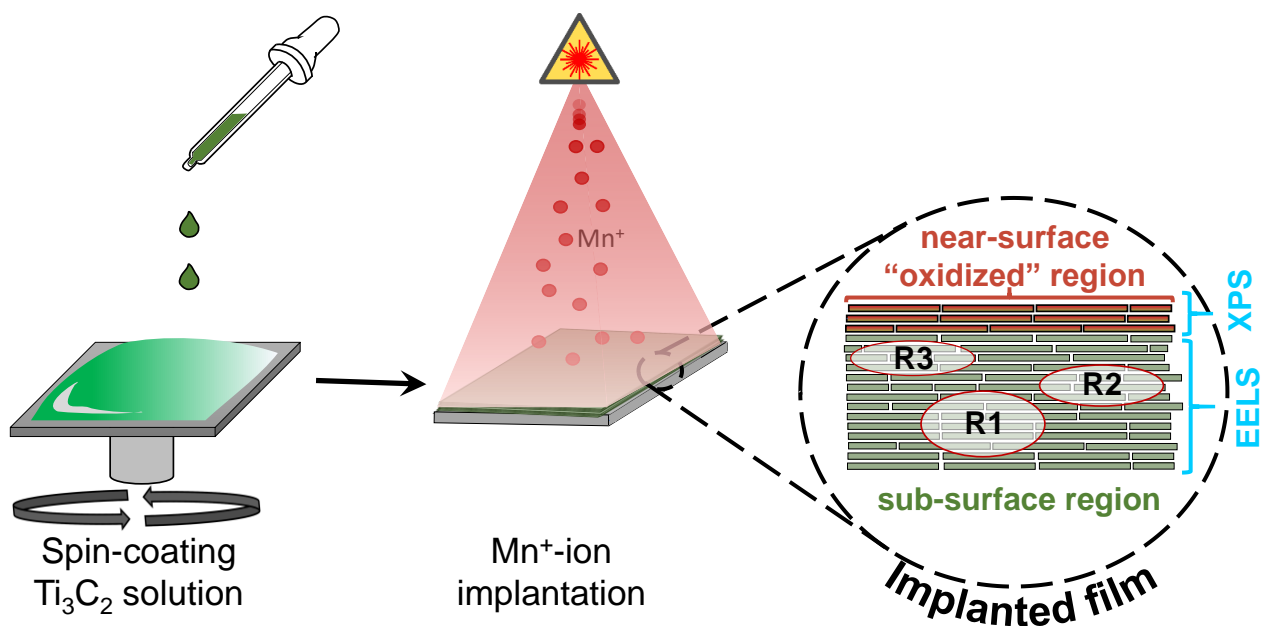


Figure S6. Schematic description of the ion implantation procedure and the implanted film “structure”, showing different regions labeled as R1-R3, used to perform electron energy loss spectroscopy analysis of implanted with $1 \cdot 10^{16}$ Mn-ions/ cm^2 $\text{Ti}_3\text{C}_2\text{T}_x$ film. The R1-R3 regions are given for a schematic illustration. The precise position of the R1-R3 fragments in the film have not been determined.

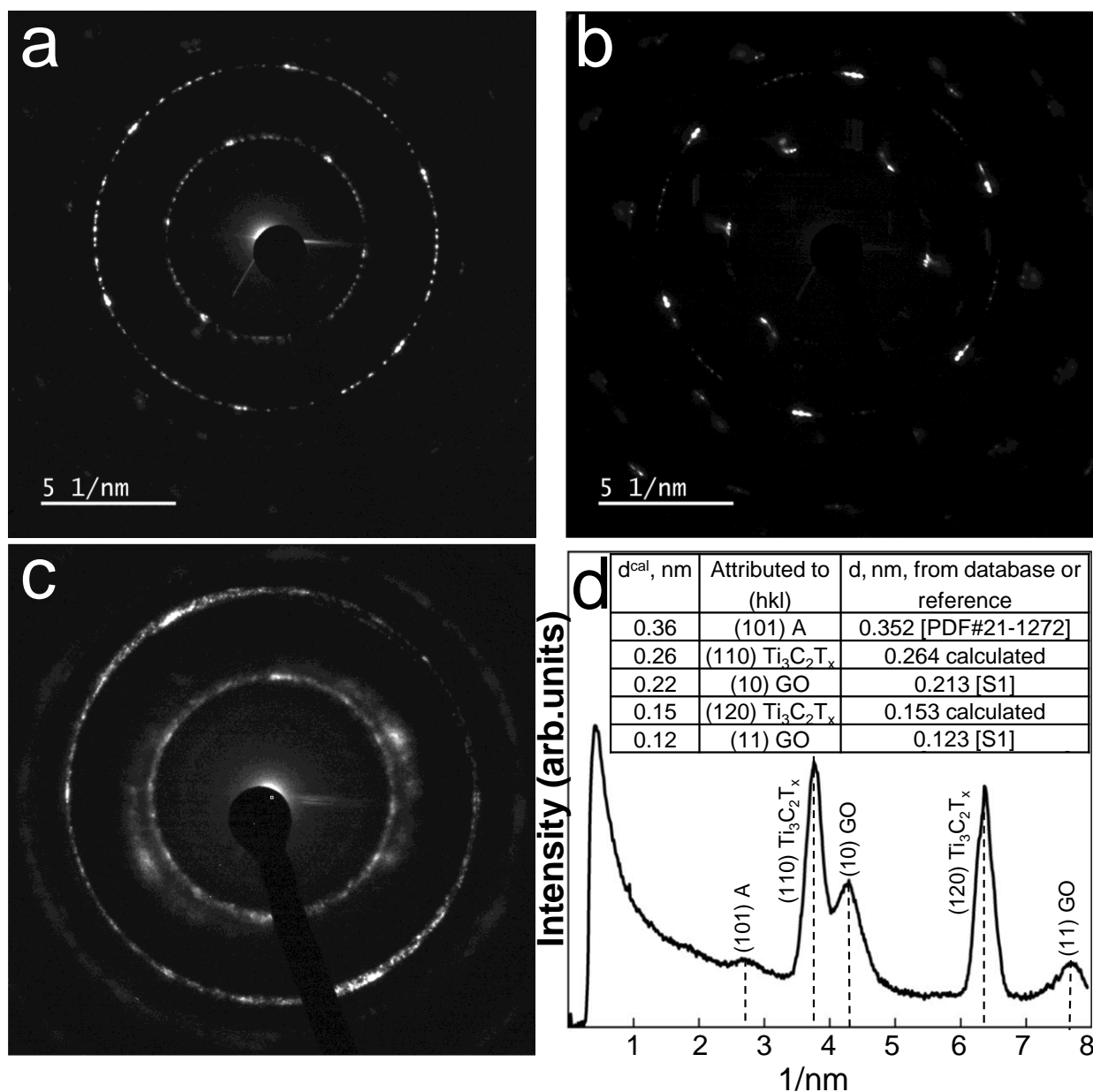


Figure S7. SAED patterns of studied **R1** (a), **R2** (b), and **R3** (c) regions extracted from different parts of sub-surface region (**Figure S5**) of $1 \cdot 10^{16}$ ions/cm² Mn-implanted $\text{Ti}_3\text{C}_2\text{T}_x$ film. (d) The radial intensity profile of the R3 region SAED pattern presented in (c). d-spacing values, d^{cal} , are calculated from experimental SAED patterns (a, b, insets). Reference values of d-spacings for anatase (A) were taken from JCPDS database – PDF#21-1272. Reference values of d-spacings for graphene oxide (GO) were taken from the Reference S1.

REFERENCES

S1 Wilson, N.; Pandey, P.A.; Beanland, R.; Rourke, J.P.; Lupo, U.; Rowlands, G.; Roemer, R.A. On the Structure and Topography of Free-Standing Chemically Modified Graphene. *New J. Phys.* **2010**, *12*, 125010.